

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	780	29/603.07,603.1,603.12,603.16,851.ccls.	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:06
S2	159	360/234.5,235.8.ccls.	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:06
S3	4233	suspension adj assembly	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:36
S4	532517	(load adj beam) or suspension or gimbal	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:07
S5	0	resin with (GALSSY ADJ CARBON)	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:08
S6	2670	glassy adj carbon	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:08
S7	474	resin with (glassy adj carbon)	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:08
S8	169	(resin with (glassy adj carbon)) same (bak\$3 or sinter\$3 or fir\$3)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 10:27
S9	5	((load adj beam) or suspension or gimbal) and ((resin with (glassy adj carbon)) same (bak\$3 or sinter\$3 or fir\$3))	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:11
S10	4233	(suspension adj assembly) and ((load adj beam) or suspension or gimbal)	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:11
S11	26	29/603.07,603.1,603.12,603.16,851.ccls. and ((suspension adj assembly) and ((load adj beam) or suspension or gimbal))	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:13
S12	277	suspension adj membrane	USPAT; JPO; DERWENT	OR	ON	2003/12/01 16:16
S13	2	(suspension adj assembly) and (suspension adj membrane)	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:14
S14	0	(suspension adj assembly) and ((resin with (glassy adj carbon)) same (bak\$3 or sinter\$3 or fir\$3))	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:14
S15	0	(suspension adj assembly) and (resin with (glassy adj carbon))	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:57

S16	19	wafer with (sacrif\$3 adj layer)	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:58
S17	217	(wafer or substrate) with (sacrif\$3 adj layer)	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:58
S18	179	((wafer or substrate) with (sacrif\$3 adj layer)) same (remov\$3 or etch\$3)	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:59
S19	0	(suspension adj assembly) and (((wafer or substrate) with (sacrif\$3 adj layer)) same (remov\$3 or etch\$3))	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:59
S20	2	((load adj beam) or suspension or gimbal) and (((wafer or substrate) with (sacrif\$3 adj layer)) same (remov\$3 or etch\$3))	USPAT; JPO; DERWENT	OR	ON	2003/12/01 15:59
S21	7	("5400192"   "5856896"   "5898541"   "5920978"   "5998906"   "6067215"   "6078473").PN.	USPAT	OR	ON	2003/12/01 16:02
S22	15	"5400192".URPN.	USPAT	OR	ON	2003/12/01 16:09
S23	3	("4636893"   "5172282"   "5212680").PN.	USPAT	OR	ON	2003/12/01 16:13
S24	1	(suspension adj membrane) with resin	USPAT; JPO; DERWENT	OR	ON	2003/12/01 16:16
S25	8216	(silicon adj substrate) with metal	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:29
S26	3580	((silicon adj substrate) with metal) and ((remov\$3 or etch\$3) with metal)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 10:24
S27	220	((silicon adj substrate) with metal) and ((remov\$3 or etch\$3) with metal with (trench or cavity))	USPAT; JPO; DERWENT	OR	ON	2003/12/02 10:24
S28	2	264/434.ccls. and (plastic adj (mold or film))	USPAT; JPO; DERWENT	OR	ON	2003/12/02 10:25
S29	1	264/434.ccls. and (mold\$3 with fill\$3 with resin)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 10:26
S30	46	mold\$3 same (resin with (glassy adj carbon)) same (bak\$3 or sinter\$3 or fir\$3)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:17
S31	0	(suspension adj assembly) and (mold\$3 same (resin with (glassy adj carbon)) same (bak\$3 or sinter\$3 or fir\$3))	USPAT; JPO; DERWENT	OR	ON	2003/12/02 10:34

S32	19	438/3.ccls. and 216/22.ccls.	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:22
S33	1245	438/3.ccls. or 216/22.ccls.	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:22
S34	55	((silicon adj substrate) with metal) and (438/3.ccls. or 216/22.ccls.)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:37
S35	28	((silicon adj substrate) with metal) and (438/3.ccls. or 216/22.ccls.)) and (cavit\$3 or tranch\$3 or hole)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:34
S36	361	((silicon adj substrate) with metal) same (cavit\$3 or tranch\$3 or hole) with (remov\$3 or etch\$3)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:36
S37	1	(438/3.ccls. or 216/22.ccls.) and ((silicon adj substrate) with metal) same (cavit\$3 or tranch\$3 or hole) with (remov\$3 or etch\$3))	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:35
S38	0	(suspension adj assembly) and ((silicon adj substrate) with metal) same (cavit\$3 or tranch\$3 or hole) with (remov\$3 or etch\$3))	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:39
S39	175571	((cavit\$3 or tranch\$3 or hole) with (remov\$3 or etch\$3))	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:36
S40	1574	((silicon adj substrate) with metal) and ( ((cavit\$3 or tranch\$3 or hole) with (remov\$3 or etch\$3)))	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:38
S41	5748	(silicon adj substrate) with (cavit\$3 or tranch\$3 or hole)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:38
S42	1966	(silicon adj substrate) with (cavit\$3 or tranch\$3 or hole) with (remov\$3 or etch\$3)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:40
S43	4236	suspension adj assembly	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:39
S44	0	((silicon adj substrate) with (cavit\$3 or tranch\$3 or hole) with (remov\$3 or etch\$3)) and (suspension adj assembly)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:39
S45	46	(silicon adj substrate) with (cavit\$3 or tranch\$3 or hole) with (remov\$3 or etch\$3) with (metal adj layer)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:40

S46	75	(silicon adj substrate) with (cavit\$3 or tranch\$3 or hole) with (remov\$3 or etch\$3) with ((metal or conductive) adj layer)	USPAT; JPO; DERWENT	OR	ON	2003/12/02 15:41
S47	3141	(substrate or web) and ((sacrificial adj (layer or material)) or (polymer\$3 adj (layer or material))) and (silicon adj (layer or material)) and ((photoresist adj (layer or material)) or mask\$3)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:14
S48	122	(substrate or web) same ((sacrificial adj (layer or material)) or (polymer\$3 adj (layer or material))) same (silicon adj (layer or material)) same ((photoresist adj (layer or material)) or mask\$3)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:27
S49	24818	(pattern\$3 or etch\$3 or remov\$3) with ((sacrificial adj (layer or material)) or (polymer\$3 adj (layer or material)))	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:15
S50	282128	(pattern\$3 or etch\$3 or remov\$3) with ((photoresist adj (layer or material)) or mask\$3)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:17
S51	6062	S49 and S50	USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:18
S52	70	S48 and S51	USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:18
S53	34	S52 and @ad<"20010114"	USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:58
S54	12	("4289846"   "4671852"   "4808549"   "5181874"   "5198385"   "5219713"   "5321685"   "5408742"   "5453404"   "5510645"   "5585722"   "5658698").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 08:27
S55	8	("6013573").URPN.	USPAT	OR	ON	2005/12/06 08:44
S56	13	Lille-Jeffrey-S.in.	USPAT	OR	ON	2005/12/06 08:44
S57	49	Lille-Jeffrey-S.in.	US-PGPUB; USPAT; JPO	OR	ON	2005/12/06 08:46
S58	0	S47 and S57	US-PGPUB; USPAT; JPO	OR	ON	2005/12/06 08:44
S59	10	S50 and S57	USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:45

S60	3	S49 and S57	USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:45
S61	11	S59 or S60	USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:45
S62	10	("4582632"   "5400192"   "5711063"   "5783326"   "5793571"   "5825590"   "5894655"   "6005750"   "6245313"   "6359752").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 08:48
S63	21	("4549238"   "5034828"   "5067037"   "5083365"   "5229193"   "5301077"   "5413850"   "5508861"   "5587857"   "5617273"   "5625512"   "5661618"   "5708540"   "5712747"   "5748408"   "5761001"   "5761790"   "5781376"   "5896244"   "6038101"   "6330131").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/12/06 08:49
S64	1	polysilsesquioxone	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:19
S65	1	(US-6013573- $\$$ ).did.	USPAT	OR	ON	2005/12/06 08:58
S66	1	S65 and (reactive near ion)	USPAT; JPO; DERWENT	OR	ON	2005/12/06 08:58
S67	45	polysilsesquioxone or MSSQ	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:40
S68	1	(polysilsesquioxone or MSSQ) near silicon	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:20
S69	0	(substrate or web) same ((sacrificial adj (layer or material)) or (polymer\$3 adj (layer or material))) same (silicon adj (layer or material)) same ((photoresist adj (layer or material)) or mask\$3) same (adhesive)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:26
S70	0	(substrate or web) same ((sacrificial adj (layer or material)) or (polymer\$3 adj (layer or material))) same (silicon adj (layer or material)) same ((photoresist adj (layer or material)) or mask\$3) same adhesive	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:28

S71	12	S57 and adhesive	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:30
S72	4	(silicon near substrate) near ((silicon or polymer) near layer) near adhesive	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:32
S73	0	(silicon adj substrate) near (polymer\$2 adj layer) near adhesive	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:33
S74	0	(silicon adj substrate) near (pol\$5 adj layer) near adhesive	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:33
S75	2722870	cur\$3 near\$3 (polysilsesquioxone or MSSQ)	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:41
S76	2	cur\$3 near (polysilsesquioxone or MSSQ)	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:43
S77	2	(cur\$3 or oxidiz\$3) near (polysilsesquioxone or MSSQ)	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:44
S78	9	(cur\$3 or oxidiz\$3) with (polysilsesquioxone or MSSQ)	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:52
S79	9	(cur\$3 or oxidiz\$3) with (poly near silsesquioxone or MSSQ)	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:53
S80	0	(poly near silsesquioxone)	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:53
S81	3	\$silsesquioxone	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:55
S82	1	\$silsesquioxone same cur\$3	USPAT; JPO; DERWENT	OR	ON	2005/12/06 09:56
S83	3	\$silsesquioxone and cur\$3	USPAT; JPO; DERWENT	OR	ON	2005/12/06 10:21
S84	2	("5711063").PN.	USPAT; USOCR; JPO; DERWENT	OR	OFF	2005/12/06 10:21
S85	24	("5711063").URPN.	USPAT	OR	ON	2005/12/06 10:22


[Home](#) | [Login](#) | [Logout](#) | [Access Information](#) | [Alerts](#) |

Welcome United States Patent and Trademark Office

**Search Results**[BROWSE](#)[SEARCH](#)[IEEE XPLORE GUIDE](#)Results for "((((head suspension assembly) <and> slider )<in>metadata)) <and> (pyr >= 1950..." [e-mail](#)Your search matched **3** of **1278046** documents.A maximum of **100** results are displayed, **25** to a page, sorted by **Relevance** in **Descending** order.

» Search Options

[View Session History](#)[New Search](#)

Modify Search

((((head suspension assembly) &lt;and&gt; slider )&lt;in&gt;metadata)) &lt;and&gt; (pyr &gt;= 1950 &lt;ar

☐ Check to search only within this results setDisplay Format: ☒ Citation ☐ Citation & Abstract

» Key

IEEE JNL IEEE Journal or Magazine

IEEE JNL IEE Journal or Magazine

IEEE CNF IEEE Conference Proceeding

IEEE CNF IEE Conference Proceeding

IEEE STD IEEE Standard

Select Article Information

- ☐ **1. Dynamics of liquid meniscus bridge of intermittent contact slider**  
Matsuoka, H.; Fukui, S.; Morishita, H.;  
Magnetics Conference, 2002. INTERMAG Europe 2002. Digest of Technical P  
International  
28 April-2 May 2002 Page(s):BQ5  
Digital Object Identifier 10.1109/INTMAG.2002.1000856  
[AbstractPlus](#) | Full Text: [PDF](#)(249 KB) IEEE CNF
- ☐ **2. Flow induced vibration of head suspension assemblies in hard drives**  
Tadepalli, S.; Anandan, P.;  
Magnetic Recording Conference, 2002. Digest of the Asia-Pacific  
27-29 Aug. 2002 Page(s):AP3-01 - AP3-02  
Digital Object Identifier 10.1109/APMRC.2002.1037629  
[AbstractPlus](#) | Full Text: [PDF](#)(223 KB) IEEE CNF
- ☐ **3. Vibration of head suspensions for proximity recording**  
Takahashi, H.; Bogy, D.B.; Matsumoto, M.;  
Magnetics, IEEE Transactions on  
Volume 34, Issue 4, Part 1, July 1998 Page(s):1756 - 1758  
Digital Object Identifier 10.1109/20.706696  
[AbstractPlus](#) | Full Text: [PDF](#)(268 KB) IEEE JNL

 Indexed by  
[Help](#) [Contact Us](#) [Privacy & ;](#)

© Copyright 2005 IEEE -